I. Introduction

THIS document serves as a starting template for writing IEEE-trans. paper in NCTU, RFVLIS-Lab.

A. First Time Usa of Latex

1) Download Miktex.
2) *Use package* MANAGER TO install the following packages:
   - All IEEE transactions/bibtex packages
   - **Textcomp**: support some symbols.
   - **amsmath**: support some maths.
   - **Subfiles**: support independent compilable subfiles .tex structure as used in this template.
   - **Dblfloatfix**: fixes double column figures ordering problems.

B. Specialized Semiconductor Process

1 Some forwords about why needs a rectifier?.
2 Focus on introduction of several representative topologies.
3 Bring up the the later sections.

C. Equation Templates

In all of the following approaches, a gate DC bias $V_{g,bias}$ is introduced as in Eq. XXXX.

$$V_{out} = N(V_{RF,Peak} - V_{th} + V_{gs,bias}).\qquad(1)$$

D. Table Templates

E. Inductive Peaking Approach

F. Other Approaches

TABLE I
SUMMARY OF THE UHF RF-TO-DC RECTIFIER PERFORMANCE.

Specification	This work	A	B	C
Frequency(MHz)	900	950	915	915
Technology	0.28μm thick-gate oxide CMOS in 65nm process	0.35μm	90nm	0.2μm
PCE@Output power	27.97%@19.3mW	15.1%@0.6μW	11%@13.1μW	71.5%@0.285mW
Number of stage / type of the rectifier	5/half-wave	1 (six stacks) / full-wave	17/half-wave	1/full-wave
Chip area	0.442mm^2	0.104mm^2	0.19mm^2	0.133mm^2